Commenton \Interaction E ects in Conductivity of Si Inversion Layers at Intermediate Temperatures"

In a recent Letter [1], Pudalov et al. have claim ed that they have found an excellent agreem ent between their experimental data and theory [2]. According to them, the anom alous (by an order of m agnitude [3]) increase of resistance with tem perature can be quantitatively described by the theory of sm all corrections arising from quantum coherent interaction e ects. Notably, this claim negates previous publication [4] entitled \Exclusion of Quantum Coherence as the Origin of the 2D Metallic State in High-M obility Silicon Inversion Layers", in which the same samples were studied in the same tem perature and density ranges. The purpose of this Com ment is to show that when analyzed correctly, the data of Pudalov et al. are not appropriate for accurate com parison with theory and do not allow one to distinguish between the interaction-based theory [2] and the traditional screening theory [5].

Despite theory [2] yields a linear-in-T correction to conductivity (), Pudalov et al. choose to analyze the temperature-dependent resistivity (). This serves to mask the fact that there is essentially no linear-in-T interval on their (T) dependences [6]. To demonstrate this, in Fig. 1 we plot (T) recalculated from the published (T) data for two lowest electron densities [7] shown in Fig. 1 (b) of R ef. [1]. The solid lines correspond to the slopes d =dT, which the authors claim to be in <code>\excellent</code> agreem ent" with their experimental data (circles). The obvious reason for the dram atic discrepancy between presentations of the data in the conductivity and resistivity form s are large changes of with temperature, reaching a factor of two.

A nother point of in portance is that the data of R ef. [1] are not related to the \anom abus increase of with tem – perature" as they are taken at (relatively) high electron densities $n_s > 2 \quad 10^{11}$ cm⁻², where interaction e ects are weak. M etallic corrections to conductivity in this regime have been observed [8] and described by the traditional screening theory [5] long time ago. The same theory provides reasonably good to to the current data from R ef. [1] (see, e.g., the dashed lines in F ig. 1). Note that at electron densities & 5 10^{11} cm⁻², theory [2] can

hardly be applied at all to Si inversion layers because surface roughness scattering becomes dominant.

Sum m arizing, the com parison perform ed by Pudalov et al. [1] between experim ental data (including those for the m agnetoresistance) and theory [2] is not valid. M oreover, their data do not support the interaction-related origin of the m etallic (T) at the relatively high electron densities used once both theories [2, 5] are treated on equal footing. As follows from accurate m easurem ents in best sam ples [3, 9], the interactions become important at low er densities close to the m etal-insulator transition, where they lead to a strong renorm alization of the effective m ass which corresponds to strongly tem perature-

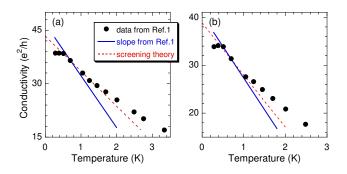


FIG.1: Conductivity vs. tem perature for $n_s = 2.46$ (a) and 2.23 10^{11} cm⁻² (b) along with the slopes d =dT recalculated from d =dT of R ef. [1]. Also shown are the ts to the data using the traditional screening theory [5] with the elective m ass values taken from R ef. [9].

dependent m etallic resistivity.

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